B. Patterning 분과

2021년 1월 28일(목), 10:45–12:15 / 채널 A

[TA2-B] Atomic Layer Etching

좌장: 이효창 박사 (KRISS)

TA2-B-1 **10:45-11:15**	[초청] **2D MoS_2 소자제조에의 ALE 응용** Ki Hyun Kim[1], Ji Eun Kang[1], Ji You Jin[1], Geun Young Yeom[1,2] *[1]School of Advanced Materials Science and Engineering, Sungkyunkwan University,* *[2]SKKU Advanced Institute of Nano Technology (SAINT), Sungkyunkwan University*
TA2-B-2 **11:15-11:30**	**Etch Characteristics of Ovonic Threshold Switch (OTS) Materials by Hydrogen Based Reactive Ion Etching (RIE)** Doo San Kim[1] and Geun Young Yeom[1,2] *[1]School of Advanced Materials Science and Engineering, Sungkyunkwan University,* *[2]SKKU Advanced Institute of Nano Technology (SAINT), Sungkyunkwan University*
TA2-B-3 **11:30-11:45**	**Atomic Layer Etching of SiO_2 with Fluoroether and Fluoroalcohol Compounds** Yongjae Kim[1], Yebin Lee[2], Seonghyeon Lee[2], and Heeyeop Chae[1,2] *[1]SKKU Advanced Institute of Nanotechnology (SAINT), Sungkyunkwan University,* *[2]School of Chemical Engineering, Sungkyunkwan University*
TA2-B-4 **11:45-12:00**	**A DFT Study on the Oxidative Etching of Ruthenium** Neung-Kyung Yu and Bonggeun Shong *Chemical Engineering, Hongik University*